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#### ABSTRACT

0042        A method for semiconductor device feature development using a bi-layer photoresist including providing a non-silicon containing photoresist layer over a substrate; providing a silicon containing photoresist over the non-silicon containing photoresist layer; exposing said silicon containing photoresist layer to an activating light source an exposure surface defined by an overlying pattern according to a photolithographic process; developing said silicon containing photoresist layer according to a photolithographic process to reveal a portion the non-silicon containing photoresist layer; and, dry developing said non-silicon containing photoresist layer in a plasma reactor by igniting a plasma from an ambient mixture including at least oxygen, carbon monoxide, and argon.